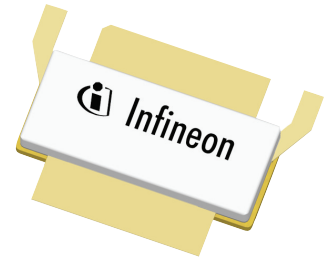


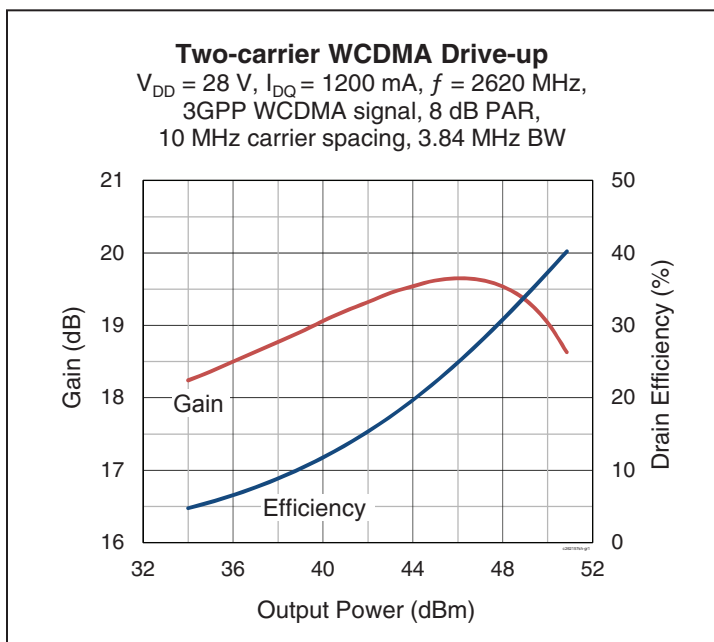
## Thermally-Enhanced High Power RF LDMOS FET 200 W, 28 V, 2620 – 2690 MHz

### Description

The PTFC262157FH LDMOS FET is designed for use in Doherty cellular power applications in the 2620 MHz to 2690 MHz frequency band. Input and output matching have been optimized for maximum performance as the peak side transistor in a Doherty amplifier. Other features include a thermally-enhanced package with earless flange. Manufactured with Infineon's advanced LDMOS process, this device provides excellent thermal performance and superior reliability.



PTFC262157FH  
Package H-34288G-4/2



### Features

- Broadband internal matching, optimized for Doherty peak side
- Wide video bandwidth
- Typical single-carrier WCDMA performance, 2690 MHz, 28 V, 10 dB PAR @ 0.01% CCDF
  - Output power at  $P_{1dB} = 50\text{ W}$
  - Efficiency = 29%
  - Gain = 19.5 dB
  - ACPR = -31.5 dBc at 2690 MHz
- Capable of handling 10:1 VSWR @ 28 V, 180 W (CW) output power
- Integrated ESD protection: Human Body Model, Class 1C (per JESD22-A114)
- Low thermal resistance
- Pb-free and RoHS compliant

### RF Characteristics

#### Single-carrier WCDMA Specifications (tested in Infineon test fixture)

$V_{DD} = 28\text{ V}$ ,  $I_{DQ} = 1150\text{ mA}$ ,  $P_{OUT} = 50\text{ W}$  average,  $f = 2690\text{ MHz}$ , 3GPP WCDMA signal, 3.84 MHz bandwidth, 10 dB PAR @ 0.01% CCDF

Characteristic	Symbol	Min	Typ	Max	Unit
Gain	Gps	18.0	19.5	—	dB
Drain Efficiency	$\eta_D$	27	29	—	%
Adjacent Channel Power Ratio	ACPR	—	-31.5	-30	dBc

All published data at  $T_{CASE} = 25^\circ\text{C}$  unless otherwise indicated

ESD: Electrostatic discharge sensitive device—observe handling precautions!

## DC Characteristics

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Drain-source Breakdown Voltage	$V_{GS} = 0\text{ V}$ , $I_{DS} = 10\text{ mA}$	$V_{(BR)DSS}$	65	—	—	V
Drain Leakage Current	$V_{DS} = 28\text{ V}$ , $V_{GS} = 0\text{ V}$	$I_{DSS}$	—	—	1.0	$\mu\text{A}$
	$V_{DS} = 63\text{ V}$ , $V_{GS} = 0\text{ V}$	$I_{DSS}$	—	—	10.0	$\mu\text{A}$
Gate Leakage Current	$V_{GS} = 10\text{ V}$ , $V_{DS} = 0\text{ V}$	$I_{GSS}$	—	—	1.0	$\mu\text{A}$
On-state Resistance	$V_{GS} = 10\text{ V}$ , $V_{DS} = 0.1\text{ V}$	$R_{DS(on)}$	—	0.05	—	$\Omega$
Operating Gate Voltage	$V_{DS} = 28\text{ V}$ , $I_{DQ} = 1.1\text{ A}$	$V_{GS}$	—	2.65	—	V

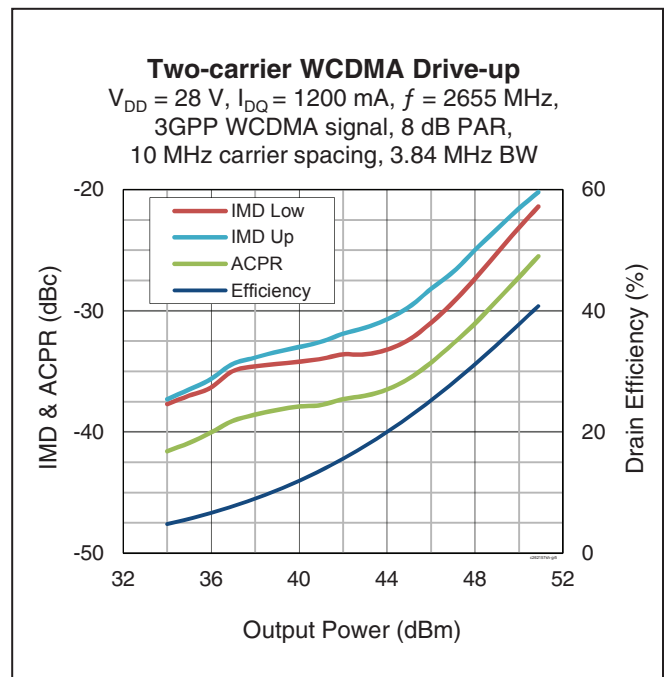
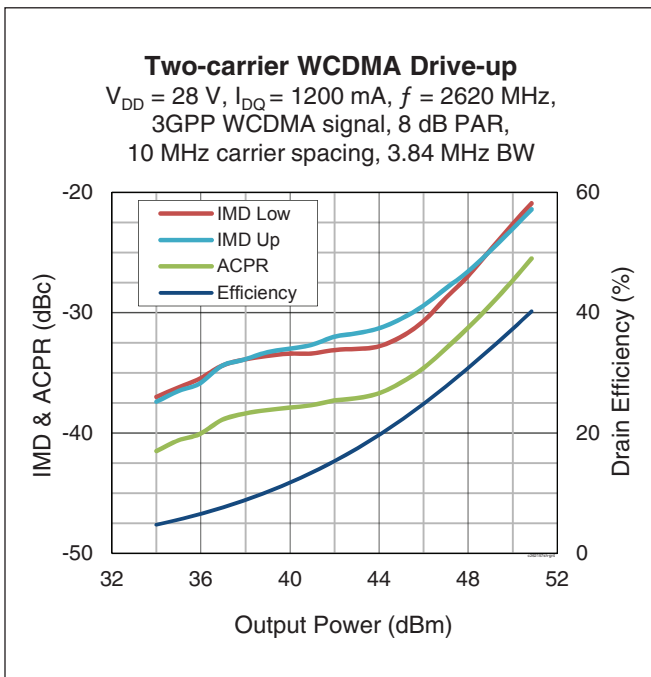
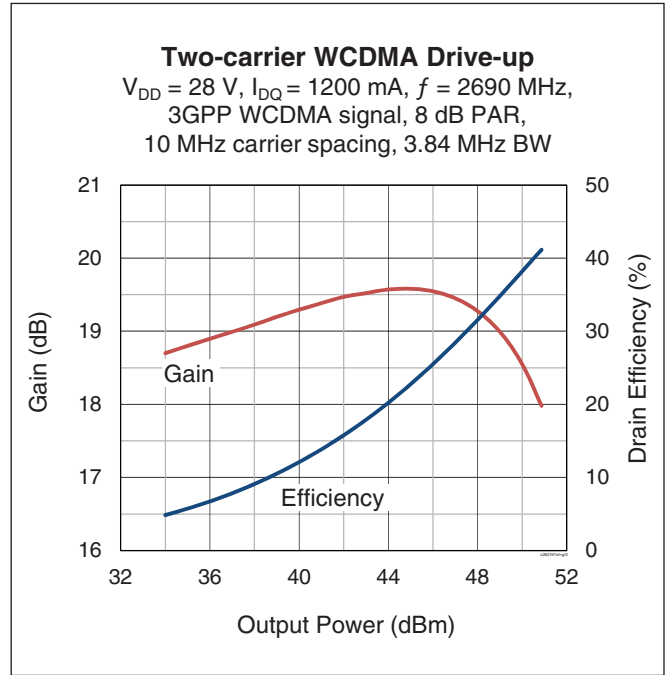
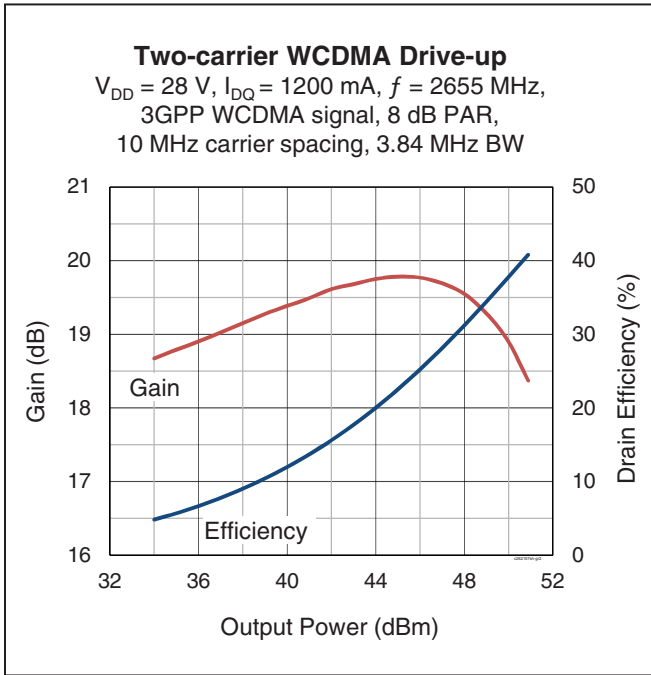
## Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source Voltage	$V_{DSS}$	65	V
Gate-source Voltage	$V_{GS}$	-6 to +10	V
Operating Voltage	$V_{DD}$	0 to +32	V
Junction Temperature	$T_J$	225	$^{\circ}\text{C}$
Storage Temperature Range	$T_{STG}$	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance ( $T_{CASE} = 70^{\circ}\text{C}$ , 150 W CW)	$R_{\theta JC}$	0.34	$^{\circ}\text{C/W}$

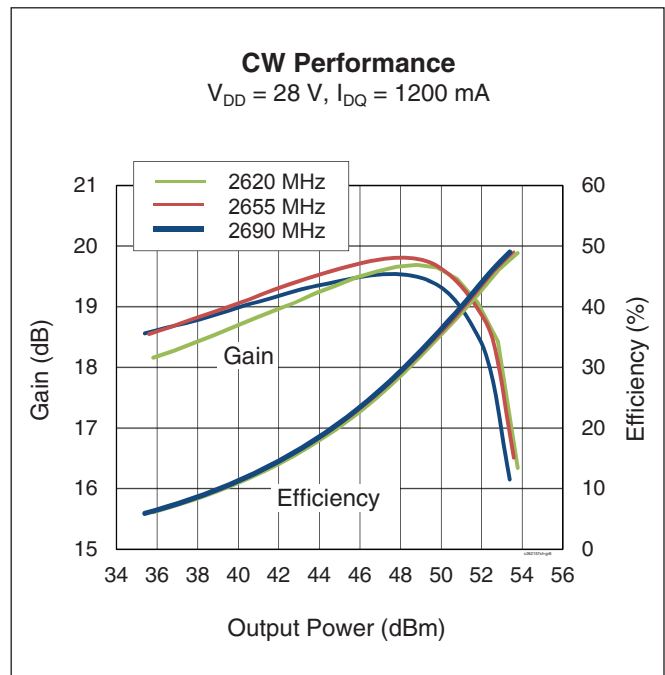
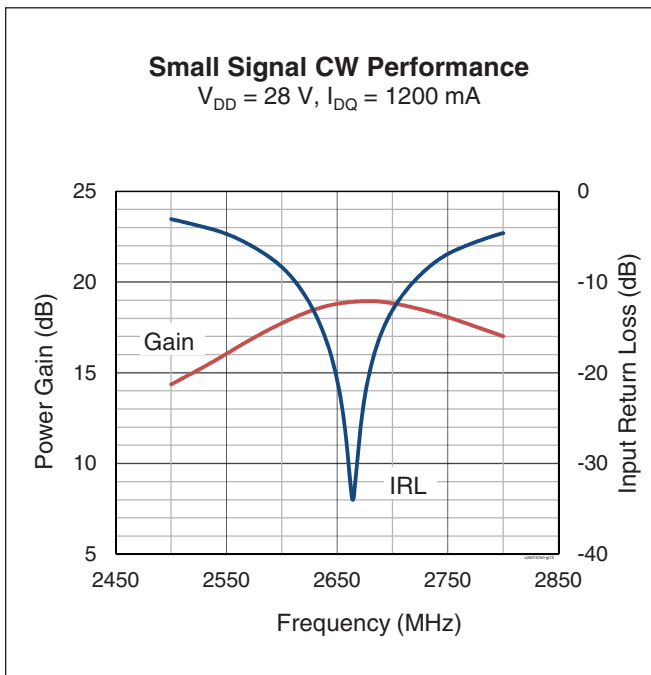
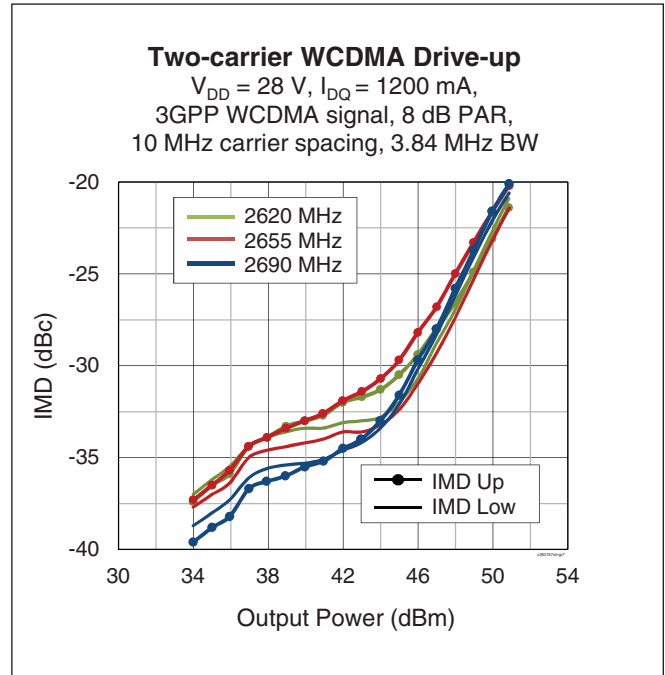
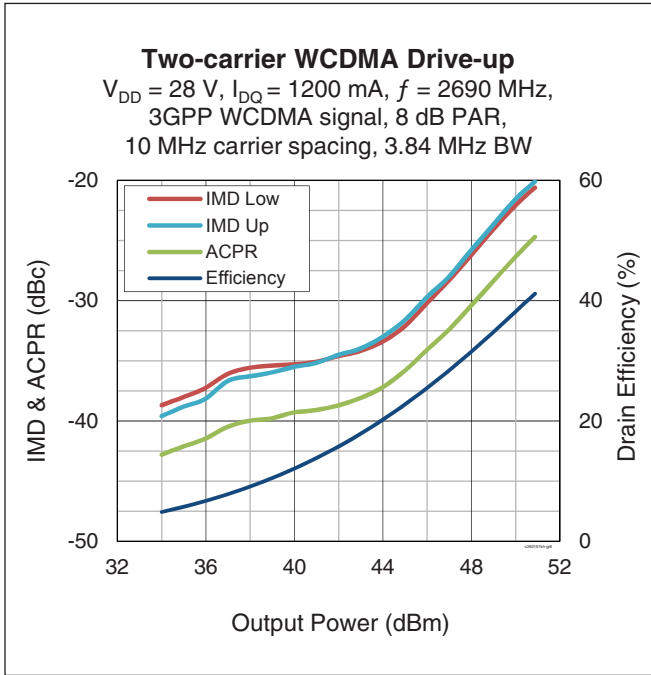
## Ordering Information

Type and Version	Order Code	Package and Description	Shipping
PTFC262157FH V1 R0	PTFC262157FHV1R0XTMA1	H-34288G-4/2, ceramic open-cavity, earless	Tape & Reel, 50 pcs
PTFC262157FH V1 R250	PTFC262157FHV1R250XTMA1	H-34288G-4/2, ceramic open-cavity, earless	Tape & Reel, 250 pcs

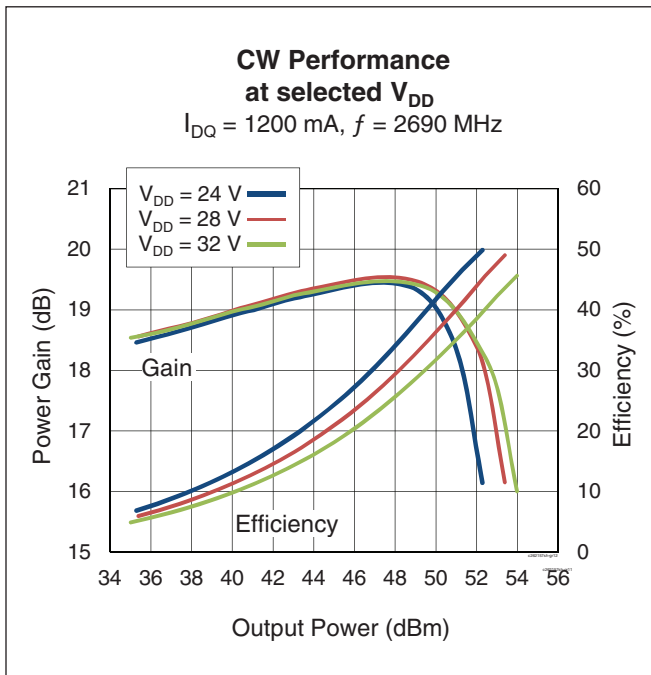
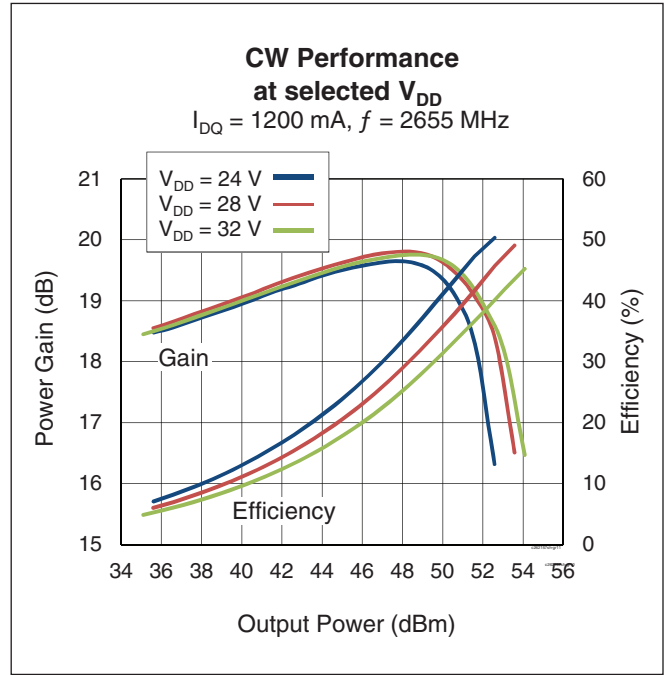
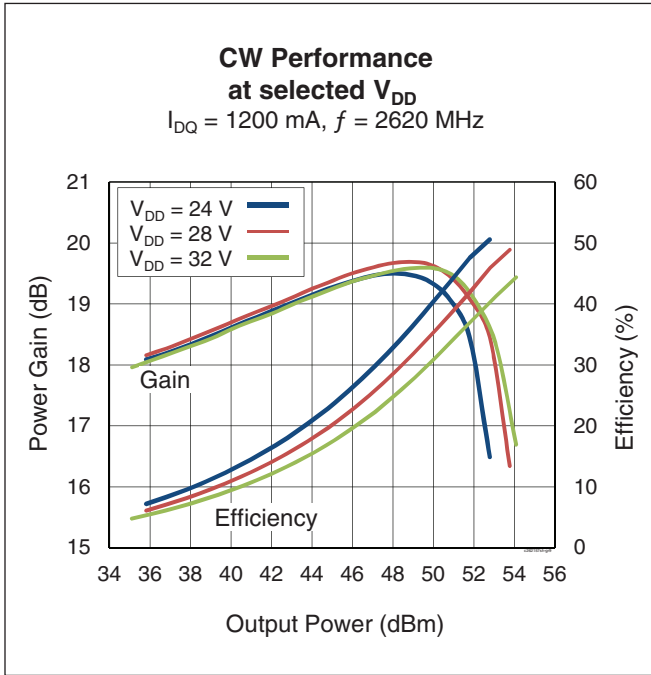
**Typical Performance** (data taken in a reference test fixture)



Typical Performance (cont.)

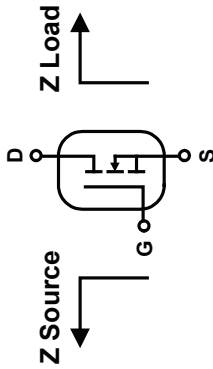


Typical Performance (cont.)



## Broadband Circuit Impedance

Frequency [MHz]	Z Source [ $\Omega$ ]	Z Load [ $\Omega$ ]
2585	2.23 – 4.85	4.41 – 3.07
2620	2.18 – 4.70	4.43 – 3.13
2655	2.13 – 4.56	4.44 – 3.18
2690	2.08 – 4.42	4.43 – 3.25
2725	2.04 – 4.28	4.41 – 3.31



## Load Pull Performance

Pulsed CW signal: 16  $\mu$ sec, 10% duty cycle; 28 V, 1100 mA

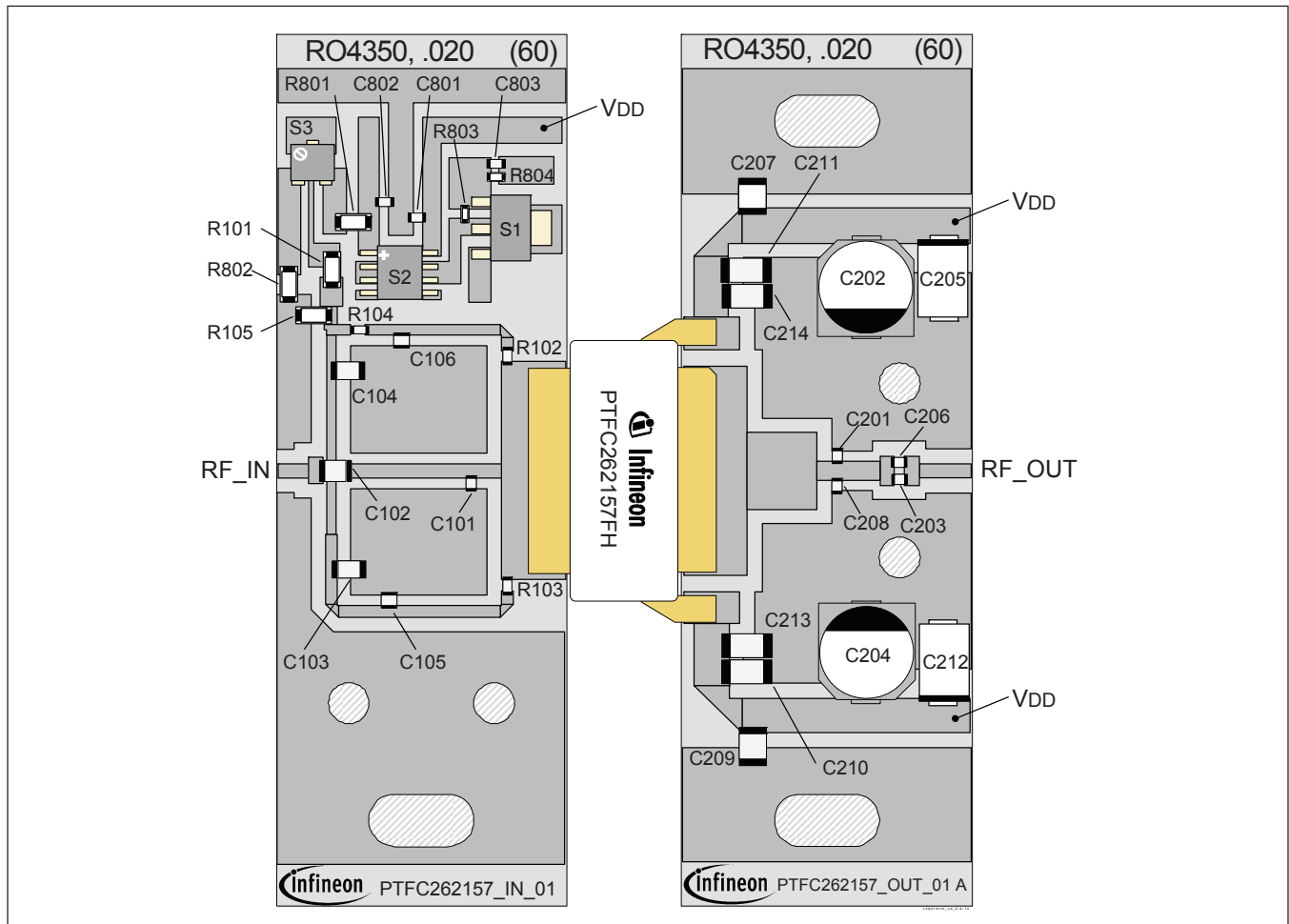
Class AB	P <sub>1dB</sub>															
	Max Output Power					Max PAE					Z Optimum					
Freq [MHz]	Zs [ $\Omega$ ]	Zi [ $\Omega$ ]	Gain [dB]	PAE [%]	P <sub>OUT</sub> [dBm]	P <sub>OUT</sub> [W]	Zi [ $\Omega$ ]	Gain [dB]	PAE [%]	P <sub>OUT</sub> [dBm]	P <sub>OUT</sub> [W]	Zi [ $\Omega$ ]	Gain [dB]	PAE [%]	P <sub>OUT</sub> [dBm]	P <sub>OUT</sub> [W]
2620	4.52 – j5.08	5.5 – j2	18.4	48.1	54.30	269	3.6 – j4.9	19.8	55.8	53.30	214	4.2 – j4.2	19.5	55.3	53.90	245
2655	7.5 – j6.07	5.5 – j1.8	18.5	48.5	54.30	269	4.2 – j4.9	19.9	56.6	53.50	224	4.4 – j4.3	19.7	56.2	53.80	240
2690	7.6 – j6.5	5.7 – j2	19.2	48.2	53.90	245	4.4 – j4.9	20.3	54.5	53.00	200	4.7 – j4	20.0	53.8	53.50	224

Pulsed CW signal: 16  $\mu$ sec, 10% duty cycle; 28 V, 50 mA

Class B	P <sub>1dB</sub>															
	Max Output Power					Max PAE					Z Optimum					
Freq [MHz]	Zs [ $\Omega$ ]	Zi [ $\Omega$ ]	Gain [dB]	PAE [%]	P <sub>OUT</sub> [dBm]	P <sub>OUT</sub> [W]	Zi [ $\Omega$ ]	Gain [dB]	PAE [%]	P <sub>OUT</sub> [dBm]	P <sub>OUT</sub> [W]	Zi [ $\Omega$ ]	Gain [dB]	PAE [%]	P <sub>OUT</sub> [dBm]	P <sub>OUT</sub> [W]
2620	3.82 – j6.78	5.9 – j2.3	17.5	54.0	54.70	295	4 – j4.7	18.4	61.2	53.90	245	4.1 – j4.4	18.3	61.1	54.10	257
2655	4.79 – j6.8	5.7 – j2.1	17.6	54.2	54.60	288	4 – j4.6	18.6	61.1	53.70	234	4.3 – j4.1	18.5	60.8	54.10	257
2690	6.28 – j6.24	5.6 – j1.8	17.7	54.2	54.50	282	4.4 – j4.6	18.6	60.5	53.60	229	4.6 – j4	18.4	60.2	54.00	251

**Reference Circuit, tuned for 2620 – 2690 MHz**

DUT	PTFC262157FH
Test Fixture Part No.	LTN/PTFC262157FH V1
PCB	Rogers 4350, 0.508 mm [.020"] thick, 2 oz. copper, $\epsilon_r = 3.66$
Find Gerber files for this reference fixture on the Infineon Web site at ( <a href="http://www.infineon.com/rfpower">http://www.infineon.com/rfpower</a> )	



Reference circuit assembly diagram (not to scale)

**Component Information**

Component	Description	Suggested Manufacturer	P/N
<b>Input</b>			
C101	Chip capacitor, 1.7 pF	ATC	ATC100A1R7CW150XB
C102	Chip capacitor, 10 pF	ATC	ATC100B100JW500XB
C103, C104	Chip capacitor, 4.7 $\mu$ F	Nichicon	F931C475MAA
C105, C106	Chip capacitor, 10 pF	ATC	ATC100A100JW500XB
C801, C802, C803	Capacitor, 1k pF	Panasonic Electronic Components	ECJ-1VB1H102K

(table cont. next page)

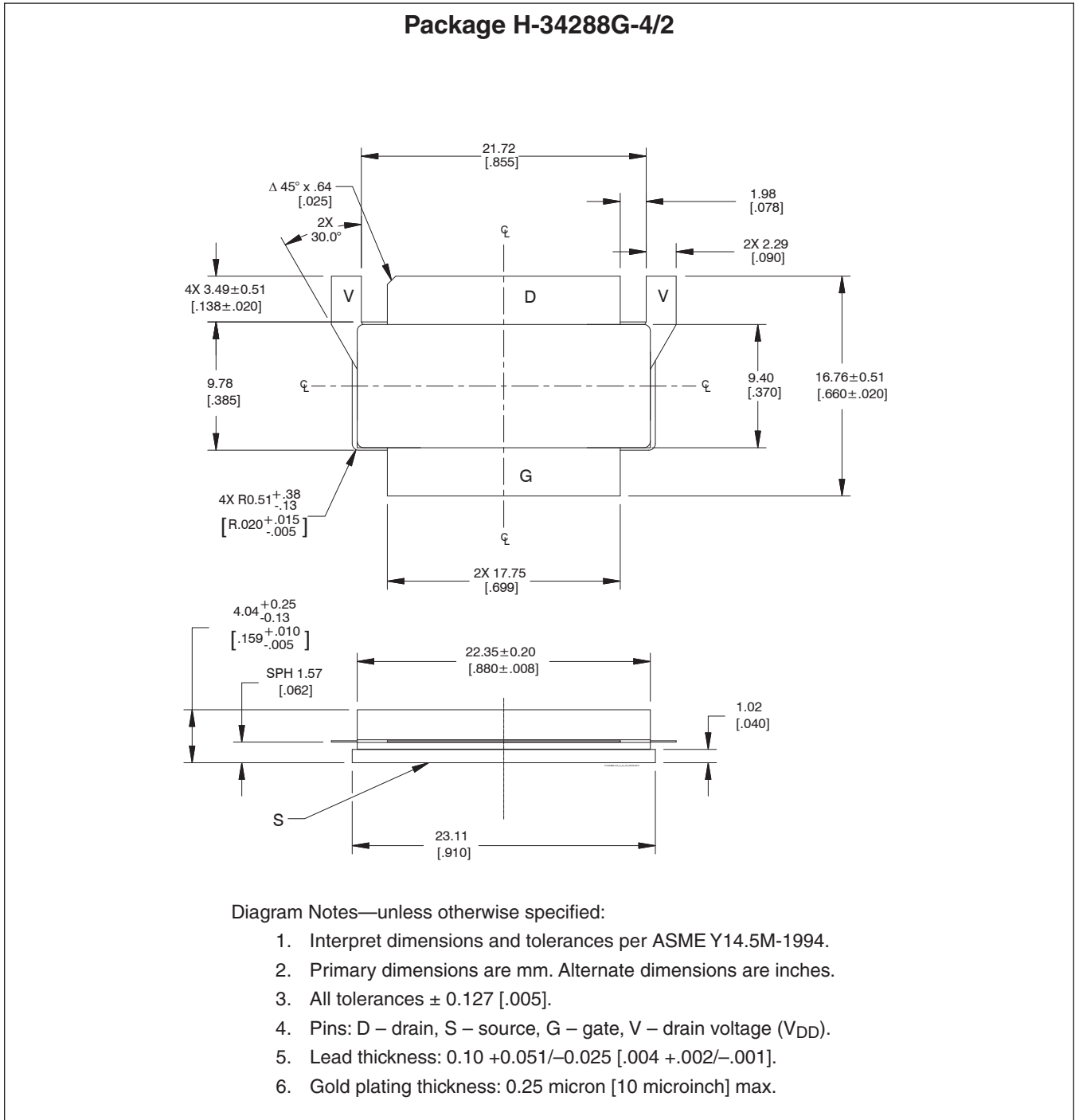
**Reference Circuit** (cont.)

**Component Information** (cont.)

<b>Component</b>	<b>Description</b>	<b>Suggested Manufacturer</b>	<b>P/N</b>
<b>Input</b> (cont.)			
R101, R802	Resistor, 10 $\Omega$	Panasonic Electronic Components	ERJ-8GEYJ100V
R102, R103, R104	Resistor, 10 $\Omega$	Panasonic Electronic Components	ERJ-3GEYJ100V
R105	Resistor, 5.1k $\Omega$	Panasonic Electronic Components	ERJ-8GEYJ512V
R801	Resistor, 100 $\Omega$	Panasonic Electronic Components	ERJ-8GEYJ101V
R803	Resistor, 1.2k $\Omega$	Panasonic Electronic Components	ERJ-3GEYJ122V
R804	Resistor, 1.2k $\Omega$	Panasonic Electronic Components	ERJ-3GEYJ132V
S1	Transistor	Infineon Technologies	BCP56-10
S2	Voltage regulator	Fairchild Semiconductor	LM7805
S3	Potentiometer, 2k $\Omega$	Bourns Inc.	3224W-1-202E
<b>Output</b>			
C201	Chip capacitor, 0.6	ATC	ATC100A0R6CW150XB
C202, C204	Capacitor, 2.2 $\mu$ F, 50 V	Panasonic Electronic Components	EEE-FP1V221AP
C203, C206	Chip capacitor, 12 pF	ATC	ATC100A120JW150XB
C205, C212	Capacitor, 10 $\mu$ F	Garrett Electronics	281M5002106K
C207, C209	Capacitor, 10 $\mu$ F	Taiyo Yuden	UMK325C7106MM-T
C208	Chip capacitor, 0.5 pF	ATC	ATC100A0R5CW150XB
C210, C211	Chip capacitor, 1 $\mu$ F	TDK Corporation	C4532X7R2A105M230KA
C213, C214	Chip capacitor, 2.2 $\mu$ F	TDK Corporation	C4532X7R1H225M160KA



Package Outline Specifications



Find the latest and most complete information about products and packaging at the Infineon Internet page ([www.infineon.com/rfpower](http://www.infineon.com/rfpower))